

RF AMPLIFIER

MODEL *TM3032*

Available as: TM3032, 4 Pin TO-8 (T4)
 TN3032, 4 Pin Surface Mount (SM3)
 FP3032, 4 Pin Flatpack (FP4)
 BX3032, Connectorized Housing (H1)

Features

- n Low Noise Figure: 2 dB Typical
- n Medium Gain: 16.5 dB Typical
- n Operating Temp. - 55 °C to +85 °C
- n Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -55 °C to +85 °C
Frequency	100 - 400 MHz	100 - 400 MHz
Gain (dB)	16.5	16.0 Min.
Power @ 1 dB Comp. (dBm)	+9.5	+8.0 Min.
Reverse Isolation (dB)	-19	-17 Max.
VSWR In	<1.75	2.0:1 Max.
Out	<1.75:1	2.0:1 Max.
Noise Figure (dB)	2.0	3.0 Max.
VSWR Vdc	+15	+15
mA	16	18 Max.

Note: Care should always be taken to effectively ground the case of each unit.

Typical Intermodulation Performance at 25 ° C

Second Order Harmonic Intercept Point +34 dBm (Typ.)
 Second Order Two Tone Intercept Point +29 dBm (Typ.)
 Third Order Two Tone Intercept Point +22 dBm (Typ.)

Maximum Ratings

Ambient Operating Temperature -55°C to + 100 °C
 Storage Temperature -62°C to + 125 °C
 Case Temperature + 125 °C
 DC Voltage + 18 Volts
 Continuous RF Input Power + 13 dBm
 Short Term RF Input Power 50 Milliwatts (1 Minute Max.)
 Maximum Peak Power 0.5 Watt (3 µsec Max.)

Typical Performance Data

